



IRF840ASPBF Information



For Reference Only

Part Number IRF840ASPBF Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 500V 8A D2PAK

Package TO-263-3, D2Pak (2 Leads + Tab), TO-263AB

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IRF840ASPBF Specifications

Manufacturer Part Number IRF840ASPBF Manufacturer Vishay Siliconix Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-263-3, D2Pak (2 Leads + Tab), TO-263AB Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 500V Current - Continuous Drain (Id) @ 25°C 8A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 38nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1018pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 3.1W (Ta), 125W (Tc) Rds On (Max) @ Id, Vgs 850 mOhm @ 4.8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB		
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Fackage TO-263-3, D2Pak (2 Leads + Tab), TO-263AB Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 500V Current - Continuous Drain (Id) @ 25°C 8A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 38nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1018pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 3.1W (Ta), 125W (Tc) Rds On (Max) @ Id, Vgs 850 mOhm @ 4.8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Manufacturer	Vishay Siliconix
PackageTO-263-3, D2Pak (2 Leads + Tab), TO-263ABSeries-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C8A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs38nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1018pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)3.1W (Ta), 125W (Tc)Rds On (Max) @ Id, Vgs850 mOhm @ 4.8A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageD2PAKPackage / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Category	Discrete Semiconductor Products
Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 500V Current - Continuous Drain (Id) @ 25°C 8A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 38nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1018pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 3.1W (Ta), 125W (Tc) Rds On (Max) @ Id, Vgs 850 mOhm @ 4.8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C8A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs38nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1018pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)3.1W (Ta), 125W (Tc)Rds On (Max) @ Id, Vgs850 mOhm @ 4.8A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageD2PAKPackage / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Package	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C8A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs38nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1018pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)3.1W (Ta), 125W (Tc)Rds On (Max) @ Id, Vgs850 mOhm @ 4.8A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageD2PAKPackage / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Series	-
Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C8A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs38nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1018pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)3.1W (Ta), 125W (Tc)Rds On (Max) @ Id, Vgs850 mOhm @ 4.8A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageD2PAKPackage / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8A (Tc) 9 8A (Tc) 9 8A (Tc) 8A (Tc) 9 8 8A (Tc) 9 8 8A (Tc) 9 8 8A (Tc) 9 8 8 8 8 8 8 8 8 8 8 8 8	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs38nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1018pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)3.1W (Ta), 125W (Tc)Rds On (Max) @ Id, Vgs850 mOhm @ 4.8A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageD2PAKPackage / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Drain to Source Voltage (Vdss)	500V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 4V @ 250μA 38nC @ 10V 1018pF @ 25V 25V 25V 25V 25V 25V 25V 25V	Current - Continuous Drain (Id) @ 25°C	8A (Tc)
Gate Charge (Qg) (Max) @ Vgs 38nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1018pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 3.1W (Ta), 125W (Tc) Rds On (Max) @ Id, Vgs 850 mOhm @ 4.8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 3.1W (Ta), 125W (Tc) Rds On (Max) @ Id, Vgs 850 mOhm @ 4.8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Gate Charge (Qg) (Max) @ Vgs	38nC @ 10V
FET Feature - Power Dissipation (Max) 3.1W (Ta), 125W (Tc) Rds On (Max) @ Id, Vgs 850 mOhm @ 4.8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Input Capacitance (Ciss) (Max) @ Vds	1018pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 850 mOhm @ 4.8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs 850 mOhm @ 4.8A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Power Dissipation (Max)	3.1W (Ta), 125W (Tc)
Mounting Type Surface Mount Supplier Device Package D2PAK Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Rds On (Max) @ Id, Vgs	850 mOhm @ 4.8A, 10V
Supplier Device Package D2PAK Package / Case D2PAK TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Mounting Type	Surface Mount
	Supplier Device Package	D2PAK
Report errors?	Package / Case	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB
		Report errors?

IRF840ASPBF Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRF840ASPBF Payment Methods





















IRF840ASPBF Shipping Methods













If you have any question about IRF840ASPBF, please do not hesitate to contact us!

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